

EMB6 / UMB6N

Transistors

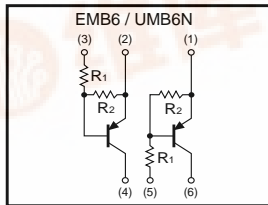
General purpose (dual digital transistors)

EMB6 / UMB6N

●Feature

1) Two DTA144E chips in a EMT or UMT package.

●Equivalent circuit



●Package, marking, and packaging specifications

Type	EMB6	UMB6N
Package	EMT6	UMT6
Marking	B6	B6
Code	T2R	TR
Basic ordering unit (pieces)	8000	3000

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Supply voltage	V _{CC}	-50	V
Input voltage	V _{IN}	-40	V
		10	
Output current	I _O	50	mA
Power dissipation	P _d	150(TOTAL)	mW *1
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55~+150	°C

*1 120mW per element must not be exceeded.

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V _{I (off)}	-	-	-0.5	V	V _{CC} =-5V, I _O =-100μA
	V _{I (on)}	-3.0	-	-		V _O =-0.3V, I _O =-2mA
Output voltage	V _{O (on)}	-	-0.1	-0.3	V	I _O =-10mA, I _I =-0.5mA
Input current	I _I	-	-	-0.18	mA	V _I =-5V
Output current	I _{O (off)}	-	-	-0.5	μA	V _{CC} =-50V, V _I =0V
DC current gain	G _I	68	-	-	-	I _O =-5mA, V _O =-5V
Input resistance	R _I	32.9	47	61.1	kΩ	-
Resistance ratio	R ₂ /R ₁	0.8	1.0	1.2	-	-
Transition frequency	f _r	-	250	-	MHz	V _{CE} =-10V, I _E =5mA, f=100MHz *

*Transition frequency of the device.

●External dimensions (Units : mm)

